

General Description:

HM6N90, the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220AB, which accords with the RoHS standard.

Features:

- I **Fast Switching**
- I **Low ON Resistance**($R_{dson} \leq 2.3\Omega$)
- I **Low Gate Charge** (Typical Data:34nC)
- I **Low Reverse transfer capacitances**(Typical:11pF)
- I **100% Single Pulse avalanche energy Test**

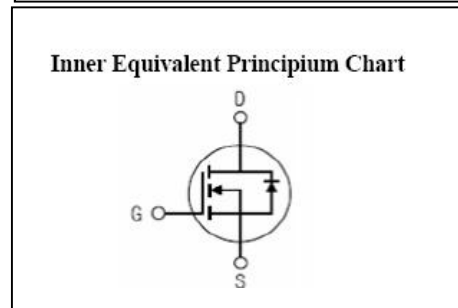
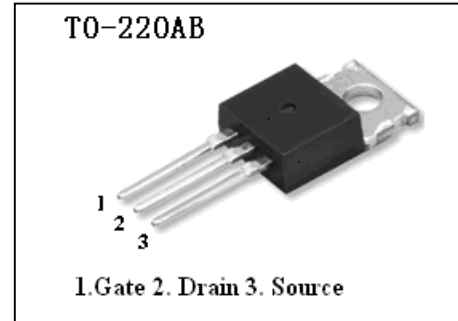
Applications:

ATX Power、LED Power.

Absolute ($T_c = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current	6	A
	Continuous Drain Current $T_c = 100^\circ\text{C}$	4	A
I_{DM}^{a1}	Pulsed Drain Current	24	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	120	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	20	mJ
I_{AR}^{a1}	Avalanche Current	2	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	120	W
	Derating Factor above 25°C	0.96	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

V_{DSS}	900	V
I_D	6	A
$P_D(T_c=25^\circ\text{C})$	120	W
$R_{DS(ON)Typ}$	1.85	Ω



Electrical Characteristics (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	900	--	--	V
ΔBV _{DSS} /ΔT _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25°C	--	0.9	--	V/°C
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 900V, V _{GS} = 0V, T _a = 25°C	--	--	25	μA
		V _{DS} = 720V, V _{GS} = 0V, T _a = 125°C	--	--	250	
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =3A	--	1.85	2.3	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Pulse width tp ≤ 300μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =15V, I _D =3A	--	7.5	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	1355	--	pF
C _{oss}	Output Capacitance		--	111	--	
C _{rss}	Reverse Transfer Capacitance		--	11	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =6A V _{DD} = 450V V _{GS} = 10V R _G =25Ω	--	20	--	ns
t _r	Rise Time		--	42	--	
t _{d(OFF)}	Turn-Off Delay Time		--	88	--	
t _f	Fall Time		--	49	--	
Q _g	Total Gate Charge	I _D =6A V _{DD} =450V V _{GS} = 10V	--	34		nC
Q _{gs}	Gate to Source Charge		--	6	--	
Q _{gd}	Gate to Drain (“Miller”)Charge		--	14	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	6	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	24	A
V_{SD}	Diode Forward Voltage	$I_S=6A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=6A, T_j = 25^\circ C$	--	220		ns
Q_{rr}	Reverse Recovery Charge	$dI_f/dt=100A/us, V_{GS}=0V$	--	1110		nC
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	1.04	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10.0mH, I_D=4.9A, Start T_j=25^\circ C$

^{a3}: $I_{SD}=6A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, Start T_j=25^\circ C$

Characteristics Curve:

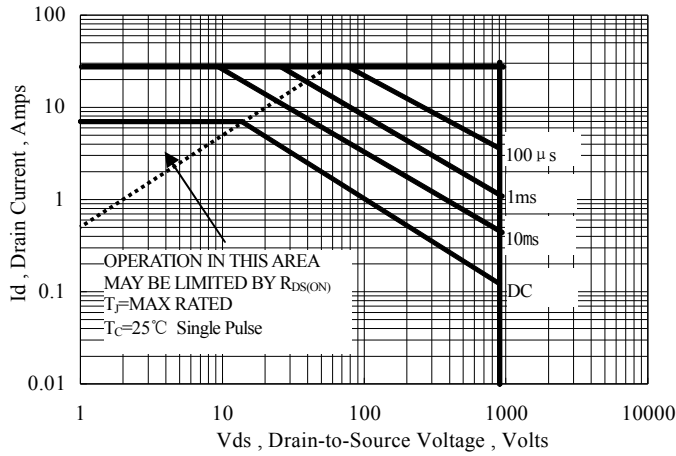


Figure 1 Maximum Forward Bias Safe Operating Area

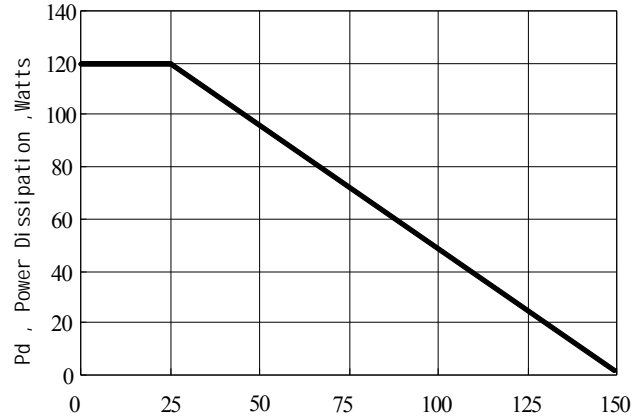


Figure 2 Maximum Power Dissipation vs Case Temperature

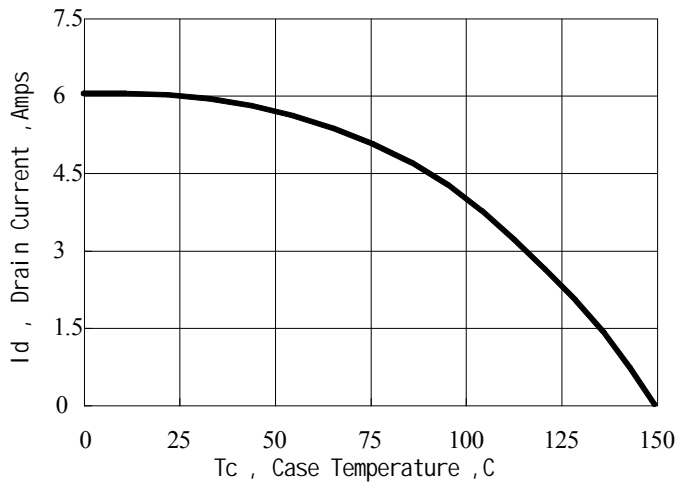


Figure 3 Maximum Continuous Drain Current vs Case Temperature

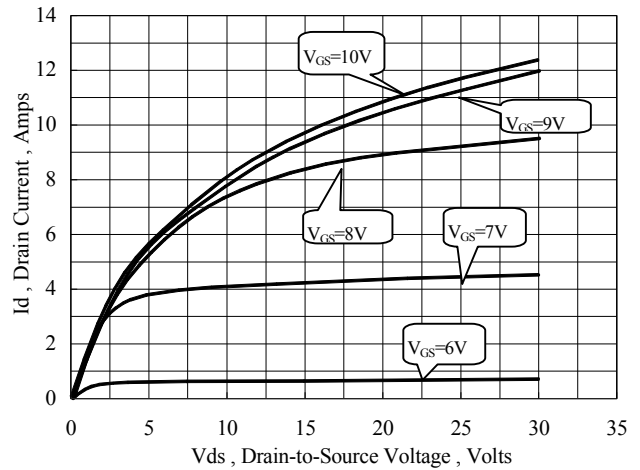
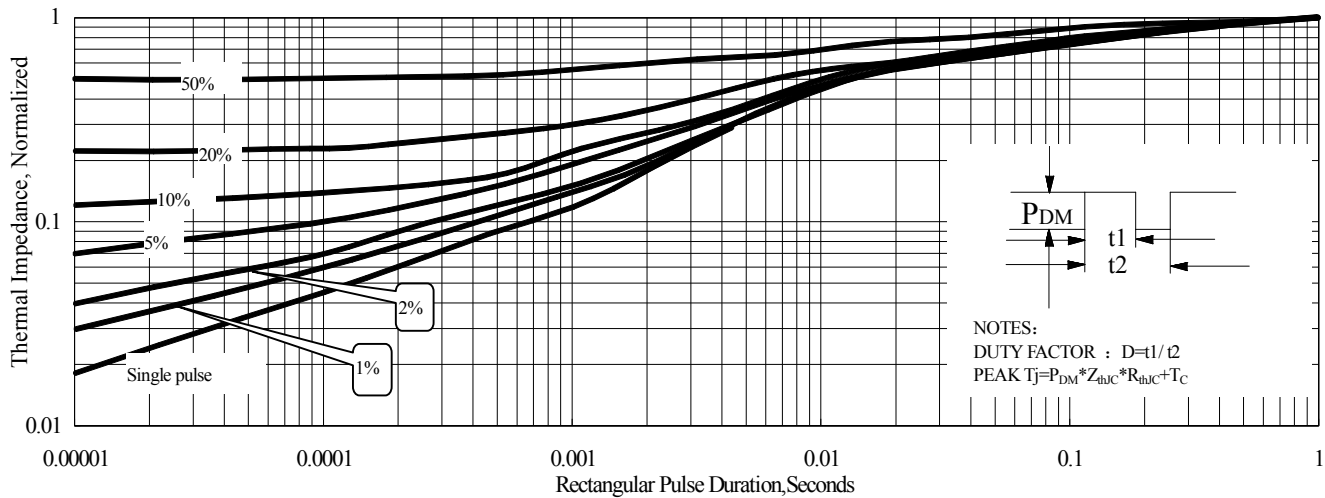


Figure 4 Typical Output Characteristics



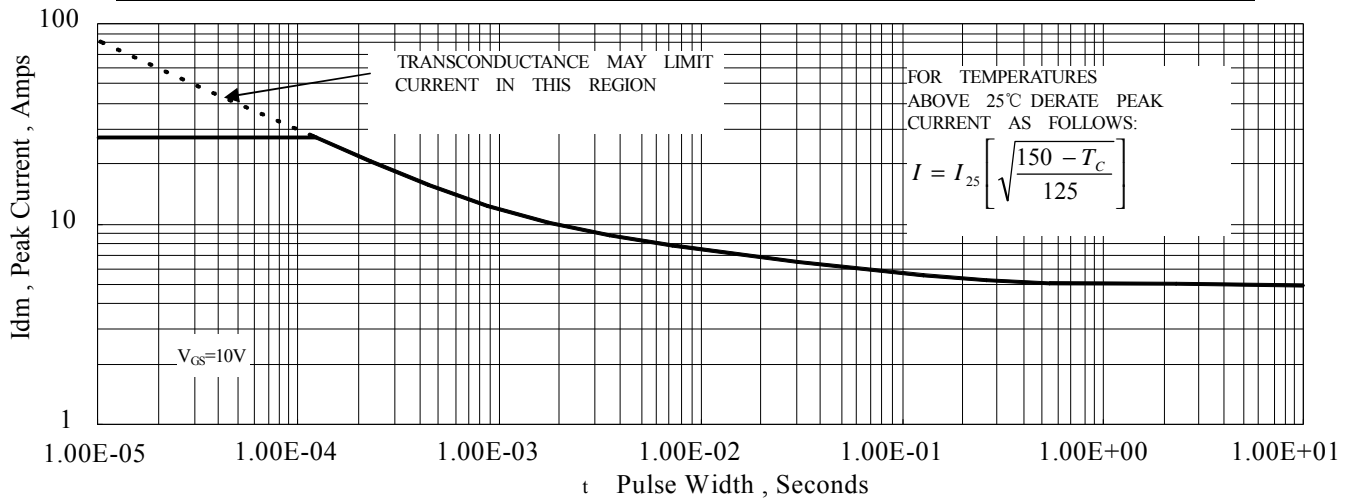


Figure 6 Maximum Peak Current Capability

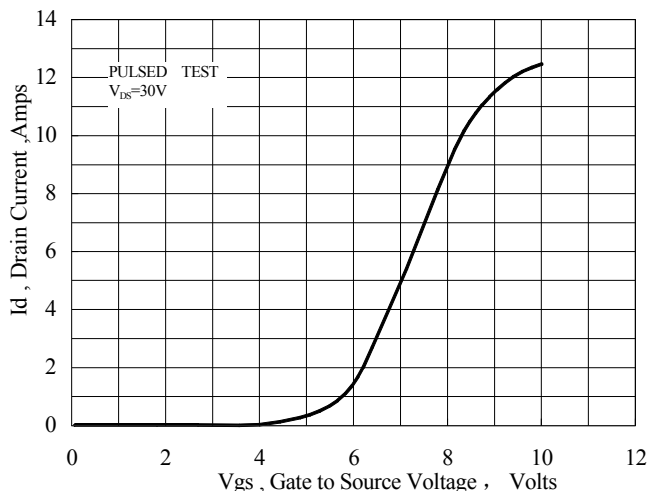


Figure 7 Typical Transfer Characteristics

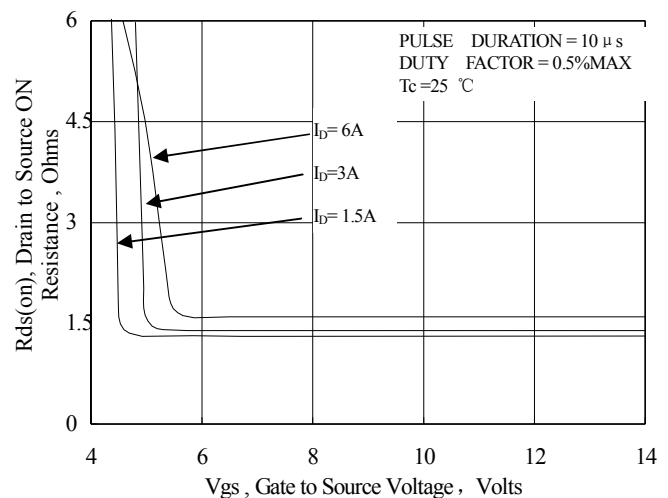


Figure 8 Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current

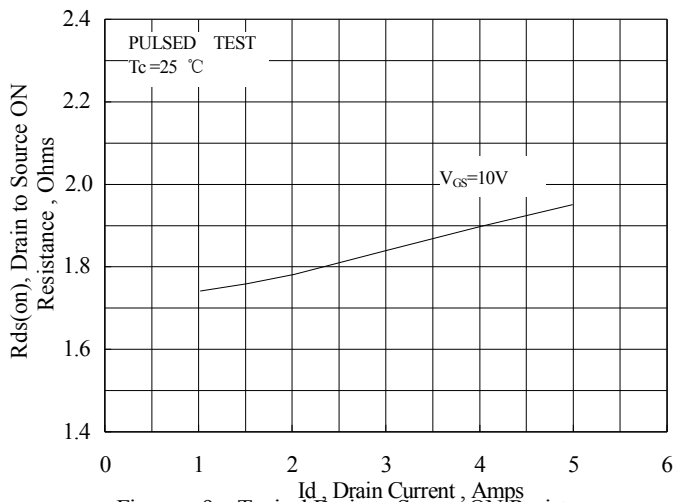


Figure 9 Typical Drain to Source ON Resistance vs Drain Current

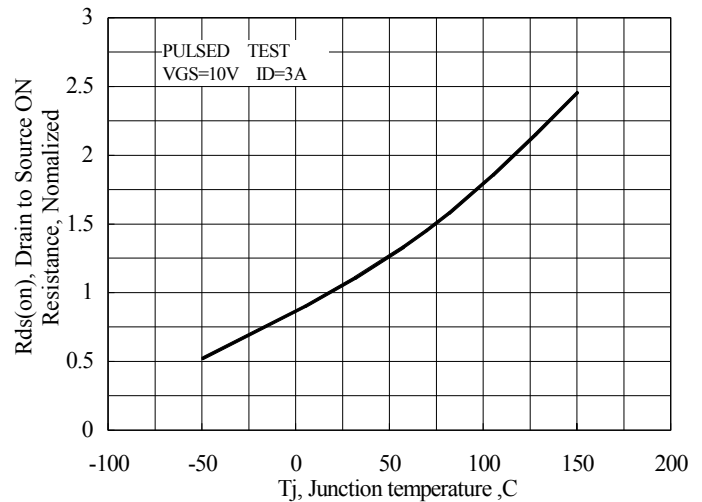


Figure 10 Typical Drain to Source ON Resistance vs Junction Temperature

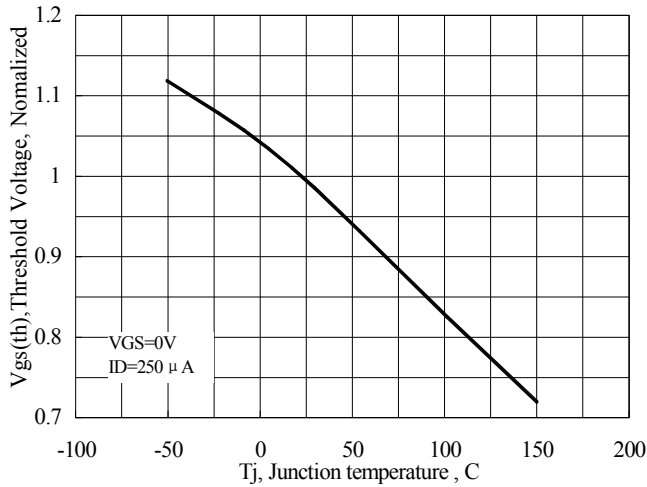


Figure 11 Typical Theshold Voltage vs Junction Temperature

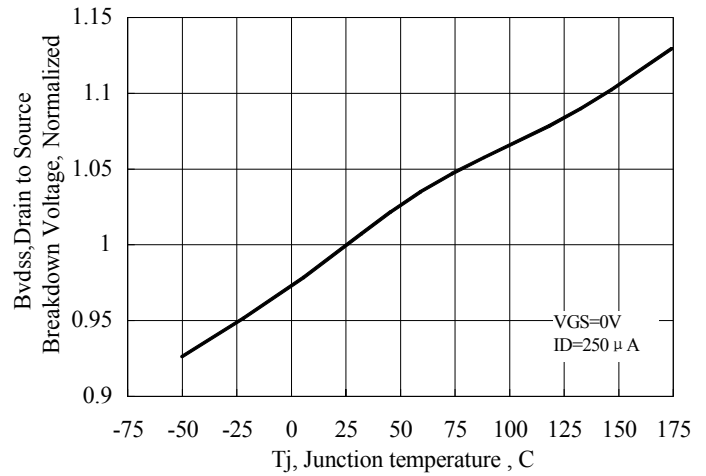


Figure 12 Typical Breakdown Voltage vs Junction Temperature

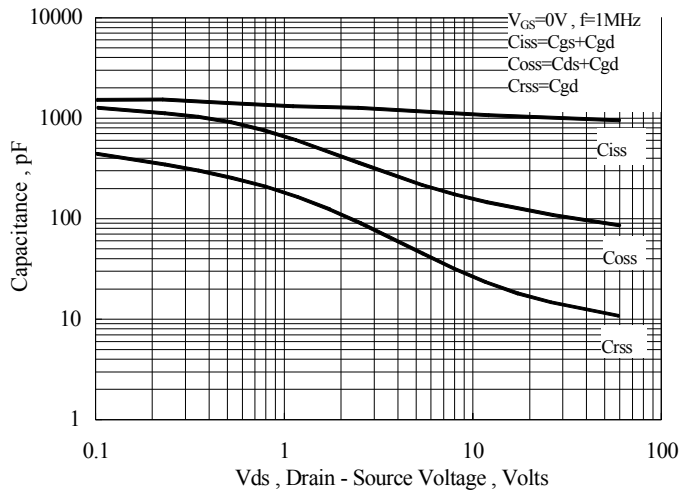


Figure 13 Typical Capacitance vs Drain to Source Voltage

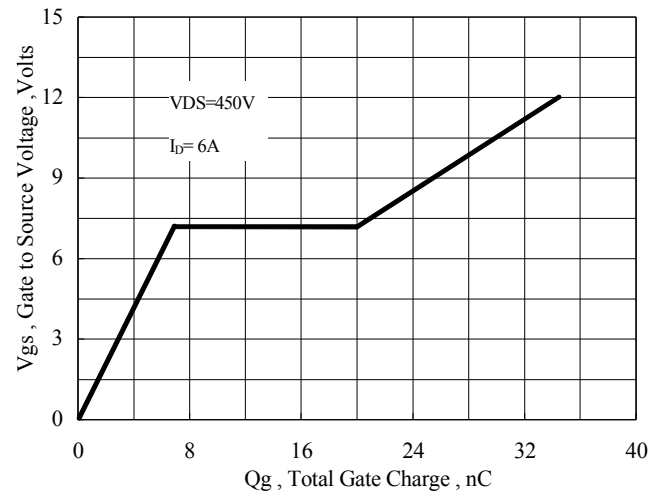


Figure 14 Typical Gate Charge vs Gate to Source Voltage

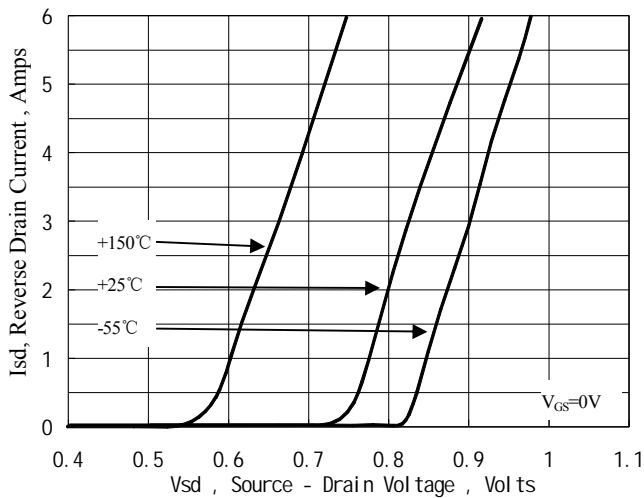


Figure 15 Typical Body Diode Transfer Characteristics

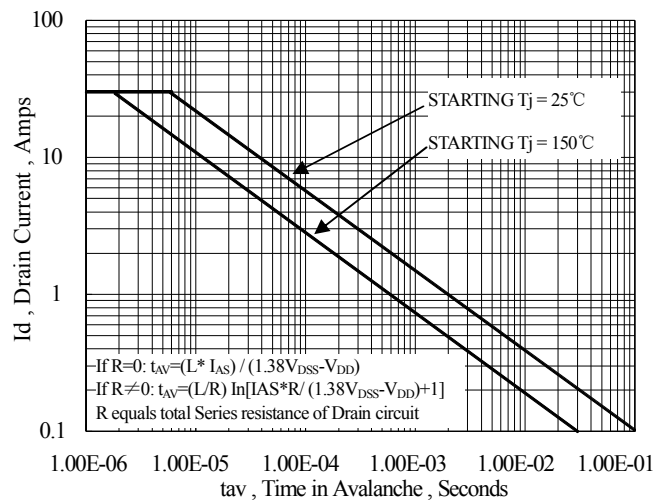


Figure 16 Unclamped Inductive Switching Capability

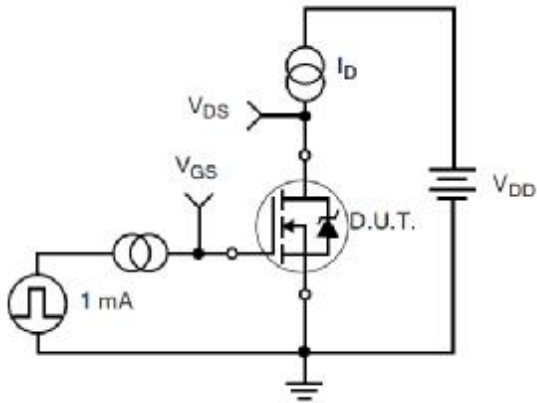


Figure 17. Gate Charge Test Circuit

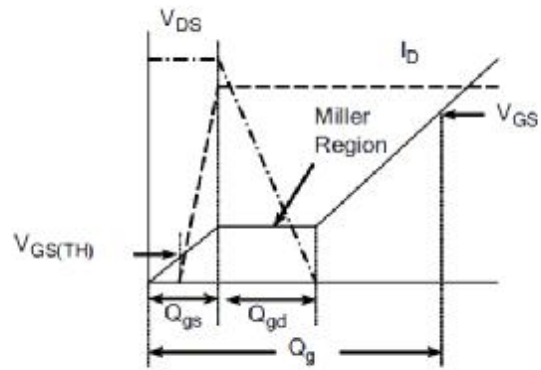


Figure 18. Gate Charge Waveform

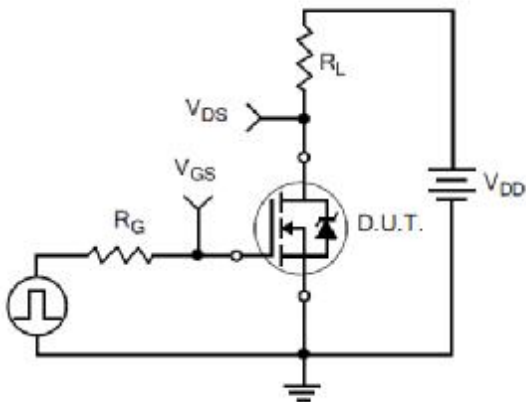


Figure 19. Resistive Switching Test Circuit

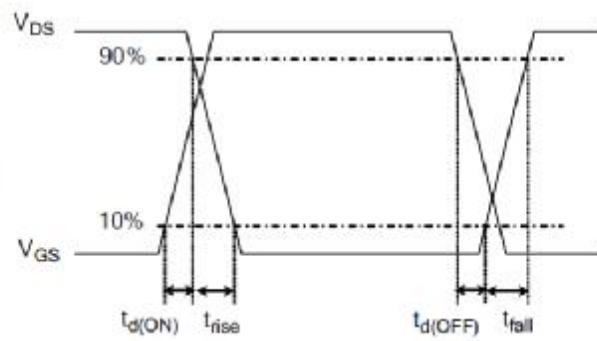


Figure 20. Resistive Switching Waveforms

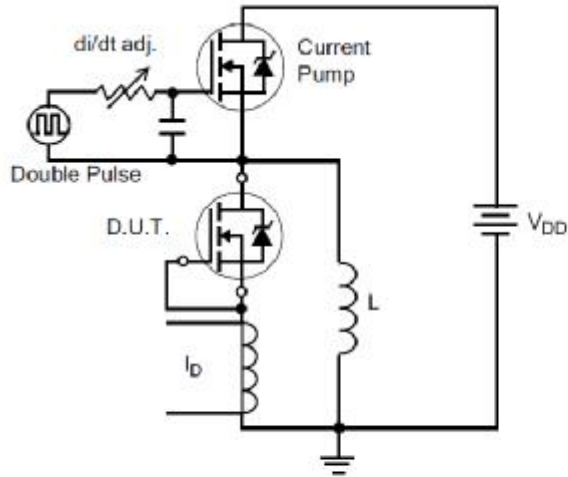


Figure 21. Diode Reverse Recovery Test Circuit

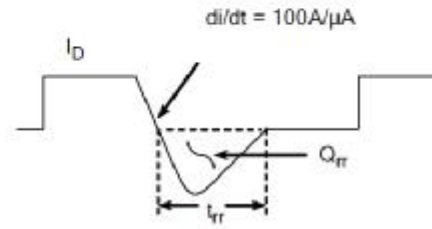


Figure 22. Diode Reverse Recovery Waveform

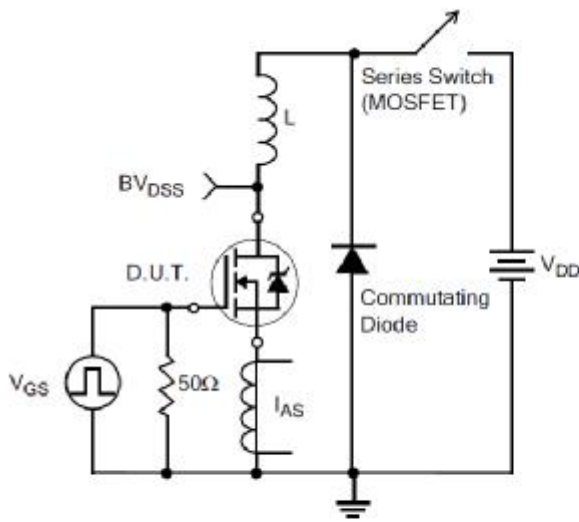


Figure 23. Unclamped Inductive Switching Test Circuit

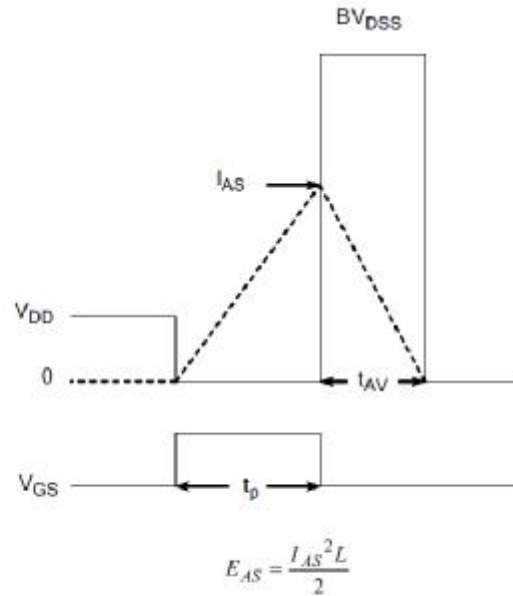
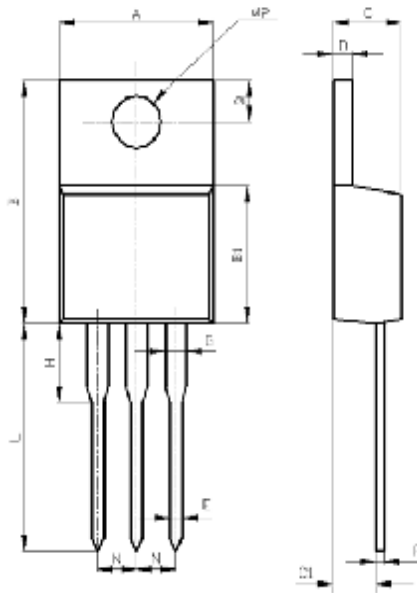


Figure 24. Unclamped Inductive Switching Waveforms



Items	Values(mm)	
	MIN	MAX
A	10.00	10.60
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	3.30	3.80
L	6.40	7.50
	6.70	7.90
	7.20	8.00
	7.50	8.60
	12.7	14.7
N	2.34	2.74
Q	2.40	3.00
ϕ P	3.50	3.90

TO-220AB Package